

Patrick Stephen Goley

List of Publications by Year in descending order

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20
papers

361
citations

933447

10
h-index

839539

18
g-index

20
all docs

20
docs citations

20
times ranked

548
citing authors

#	ARTICLE	IF	CITATIONS
1	Modeling Transient Loss Due to Ionizing Particles in Silicon Photonic Waveguides. IEEE Transactions on Nuclear Science, 2022, 69, 518-526.	2.0	1
2	Localized Excitation of Silicon Photonic Waveguides for Measurement of Free-Carrier Lifetime and Surface Recombination Velocity. , 2021, , .		1
3	Optical Single-Event Transients Induced in Integrated Silicon-Photonic Waveguides by Two-Photon Absorption. IEEE Transactions on Nuclear Science, 2021, 68, 785-792.	2.0	14
4	Zero-Process-Change SiGe Heterojunction Avalanche Photodiode for High-Speed, High-Gain Detection Near the Silicon Band Edge. IEEE Electron Device Letters, 2021, 42, 1260-1263.	3.9	0
5	Design, Theoretical, and Experimental Investigation of Tensile-Strained Germanium Quantum-Well Laser Structure. ACS Applied Electronic Materials, 2021, 3, 4535-4547.	4.3	13
6	Response of Waveguide-Integrated Germanium-on-Silicon p-i-n Photodiodes to Neutron Displacement Damage. IEEE Transactions on Nuclear Science, 2020, 67, 296-304.	2.0	6
7	Comparison of Single-Event Transients in SiGe HBTs on Bulk and Thick-Film SOI. IEEE Transactions on Nuclear Science, 2020, 67, 71-80.	2.0	7
8	Electronic-to-Photonic Single-Event Transient Propagation in a Segmented Mach-Zehnder Modulator in a Si/SiGe Integrated Photonics Platform. IEEE Transactions on Nuclear Science, 2020, 67, 260-267.	2.0	3
9	Single-Event Transients in SiGe HBTs Induced by Pulsed X-Ray Microbeam. IEEE Transactions on Nuclear Science, 2020, 67, 91-98.	2.0	4
10	Total Ionizing Dose Effects in 70-GHz Bandwidth Photodiodes in a SiGe Integrated Photonics Platform. IEEE Transactions on Nuclear Science, 2019, 66, 125-133.	2.0	11
11	Potential Limitations on Integrated Silicon Photonic Waveguides Operating in a Heavy Ion Environment. IEEE Transactions on Nuclear Science, 2018, 65, 141-148.	2.0	18
12	Strain-Engineered Biaxial Tensile Epitaxial Germanium for High-Performance Ge/InGaAs Tunnel Field-Effect Transistors. IEEE Journal of the Electron Devices Society, 2015, 3, 184-193.	2.1	33
13	Heterogeneously-Grown Tunable Tensile Strained Germanium on Silicon for Photonic Devices. ACS Applied Materials & Interfaces, 2015, 7, 26470-26481.	8.0	23
14	Mixed-anion GaAs _{1-x} Sb _x graded buffer heterogeneously integrated on Si by molecular beam epitaxy. Applied Physics Express, 2015, 8, 025501.	2.4	4
15	Heterointerface Engineering of Broken-Gap InAs/GaSb Multilayer Structures. ACS Applied Materials & Interfaces, 2015, 7, 2512-2517.	8.0	21
16	Heteroepitaxial Ge MOS Devices on Si Using Composite AlAs/GaAs Buffer. IEEE Journal of the Electron Devices Society, 2015, 3, 341-348.	2.1	16
17	Integration of SrTiO ₃ on Crystallographically Oriented Epitaxial Germanium for Low-Power Device Applications. ACS Applied Materials & Interfaces, 2015, 7, 5471-5479.	8.0	22
18	Magnetotransport Properties of Epitaxial Ge/AlAs Heterostructures Integrated on GaAs and Silicon. ACS Applied Materials & Interfaces, 2015, 7, 22315-22321.	8.0	9

#	ARTICLE	IF	CITATIONS
19	Germanium Based Field-Effect Transistors: Challenges and Opportunities. <i>Materials</i> , 2014, 7, 2301-2339.	2.9	129
20	Heterogeneous Integration of Epitaxial Ge on Si using AlAs/GaAs Buffer Architecture: Suitability for Low-power Fin Field-Effect Transistors. <i>Scientific Reports</i> , 2014, 4, 6964.	3.3	26